SILICON PLANAR EPITAXIAL N-P-N TRANSISTOR

BF195

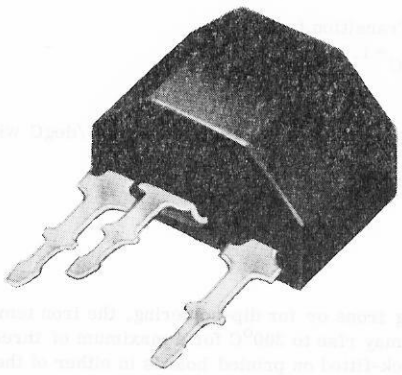
TENTATIVE DATA

N-P-N low noise transistor in epoxy resin encapsulation with three rigid self-locking strips suitable for insertion into printed circuit boards using standard grids. The transistor is recommended for use in the input stages of a.m./f.m. receivers, also for use in mixer and i.f. stages of a.m. battery operated receivers.

QUICK REFERENCE DATA		
V_{CBO} max.	30	V
V_{CEO} max.	20	V
I_C max.	30	mA
P_{tot} max.	220	mW
T_j max.	125	°C
h_{FE} typ. (I_C=1.0mA, V_{CE}=10V)	67	
f_T typ. (I_C=1.0mA, V_{CE}=10V)	200	MHz
N typ. (I_C=1.0mA, V_{CE}=10V, g_s=20mmho, f=1.0MHz)	3.5	dB
(I_C=1.0mA, V_{CE}=10V, g_s=10mmho, f=100MHz)	4.0	dB

OUTLINE AND DIMENSIONS

For details see page 4



RATINGS

Limiting values of operation according to the absolute maximum system.

Electrical

V_{CBO} max. (I_E=0)	30	V
V_{CEO} max. (I_B=0, see curve on page 7)	20	V
V_{EBO} max. (I_C=0)	5.0	V
I_C max.	30	mA
I_{CM} max.	30	mA
P_{tot} max. (T_{amb}≤25°C)	220	mW

Temperature

T_{stg} min.	-65	°C
T_{stg} max.	125	°C
T_j max.	125	°C

THERMAL CHARACTERISTIC

$R_{th(j-amb)}$	0.45	degC/mW

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise stated)

		Min.	Typ.	Max.	
$-V_{BE}$	Base-emitter voltage (see note 1) I_C=1.0mA, V_{CE}=10V	650	-	740	mV
I_B	Base current I_C=1.0mA, V_{CE}=10V	8.0	15	28	μA
$-C_{re}$	Feedback capacitance I_C=1.0mA, V_{CE}=10V, f=0.45MHz	-	0.95	-	pF
f_T	Transition frequency I_C=1.0mA, V_{CE}=10V	-	200	-	MHz

NOTE

1. V_{BE} decreased by approximately 1.7mV/degC with increasing temperature.

SOLDERING NOTE

For soldering irons or for dip-soldering, the iron temperature or solder temperature may rise to 300°C for a maximum of three seconds, with the transistor lock-fitted on printed boards in either of the possible mounting positions.

ELECTRICAL CHARACTERISTICS (cont'd)

		Min.	Typ.	Max.	
N	Noise figure				
	I_C=1.0mA, V_{CE}=10V,				
	g_s=20mmho, f=1.0MHz	-	3.5	-	dB
	g_s=10mmho, f=100MHz	-	4.0	-	dB
N_c	Conversion noise figure				
	I_C=1.0mA, V_{CE}=10V,				
	g_s=1.2mmho, f=0.2MHz	-	4.0	-	dB
	g_s=1.5mmho, f=1.0MHz	-	2.5	-	dB

Typical y-parameters

Common base

I_C=1.0mA, V_{CE}=10V, f=100MHz, lead length=3.0mm

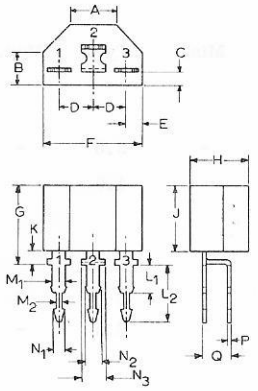
g_{ib}	Input conductance	38	mmho
$-b_{ib}$	Input susceptance	1.0	mmho
$\lvert y_{rb} \rvert$	Feedback admittance	440	μmho
ϕ_{rb}	Phase angle of feedback admittance	275	deg
$\lvert y_{fb} \rvert$	Transfer admittance	34	mmho
ϕ_{fb}	Phase angle of transfer admittance	140	deg
g_{ob}	Output conductance	12	μmho
b_{ob}	Output susceptance	1.1	mmho

Common emitter

I_C=1.0mA, V_{CE}=10V, lead length=3.0mm

		f =	10.7	0.45	MHz
g_{ie}	Input conductance		<0.96	<0.86	mmho
g_{oe}	Output conductance		<9.5	<7.0	μmho

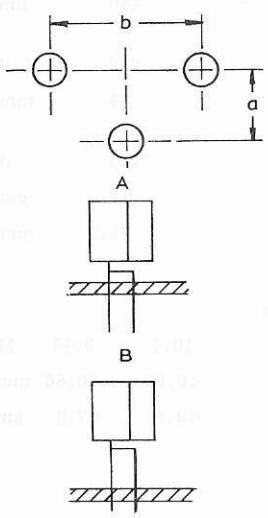
OUTLINE AND DIMENSIONS



	Millimetres	
	Min.	Max.
A	3.4	3.6
B	2.4	2.6
C	0.8	1.1
D	2.44	2.64
E	1.1	1.3
F	7.4	7.6
G	6.0	6.4
H	4.4	4.6
J	4.9	5.1
K	1.0	1.3
L1	2.1	2.2
L2	4.0	4.3
M1	0.65	0.80
M2	0.45	0.60
N1	0.70	0.80
N2	1.15	1.25
N3	1.75	2.00
P	0.17	0.25
Q	1.75	2.00

Pin connections
1. Base
2. Emitter
3. Collector

Mounting details



a = 2.49 to 2.59mm

b = 5.03 to 5.13mm

Maximum thickness of printed board = 1.7mm

Hole diameter = 1.25 to 1.35mm

Maximum thickness of printed board = 1.1mm

Hole diameter = 0.77 to 0.83mm

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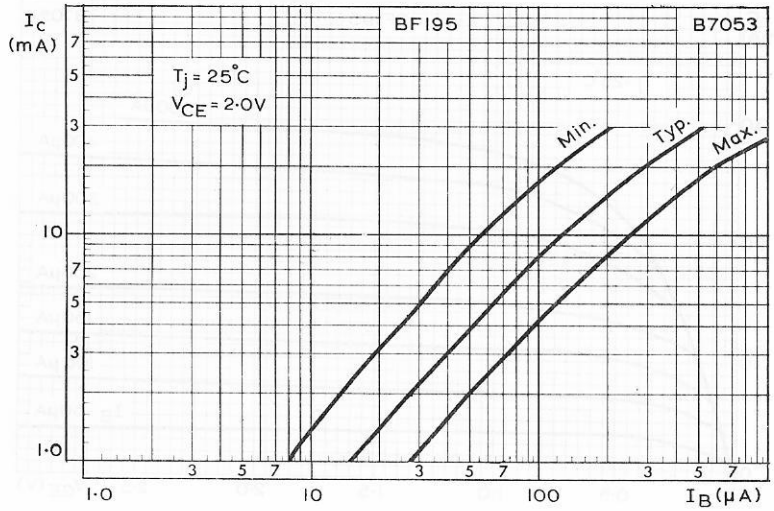
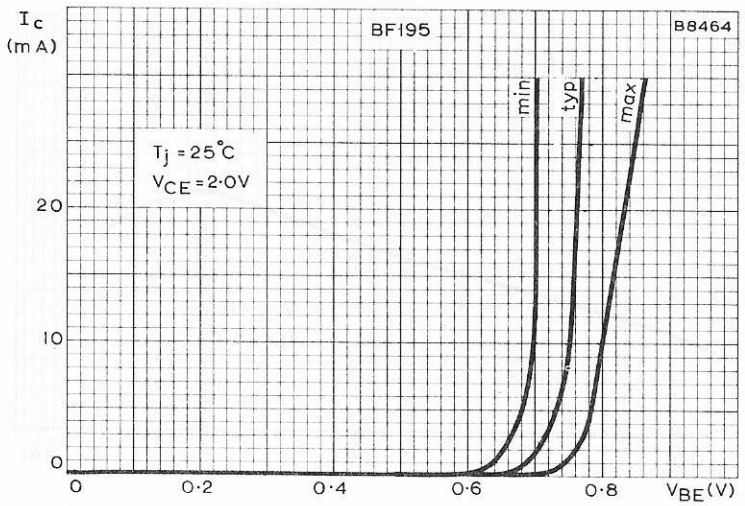
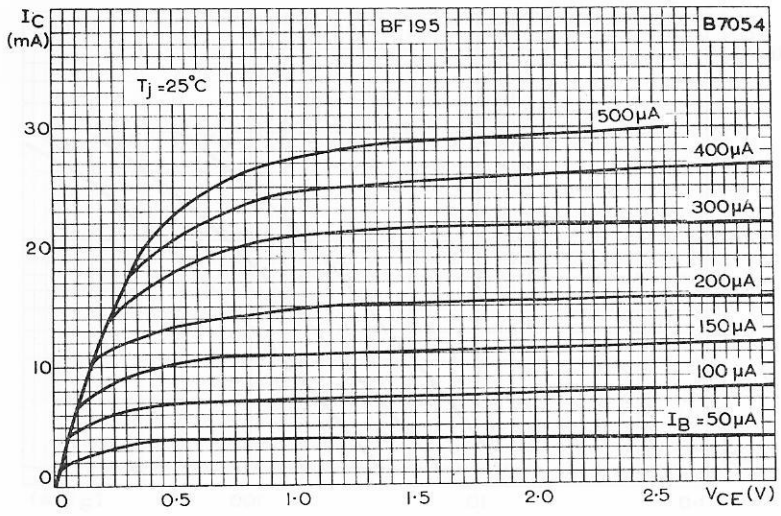


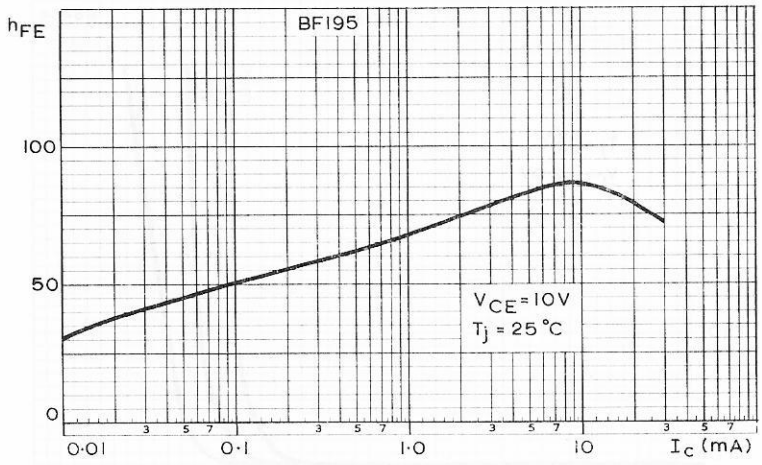
TRANSFER CHARACTERISTICS. $T_j = 25^oC$



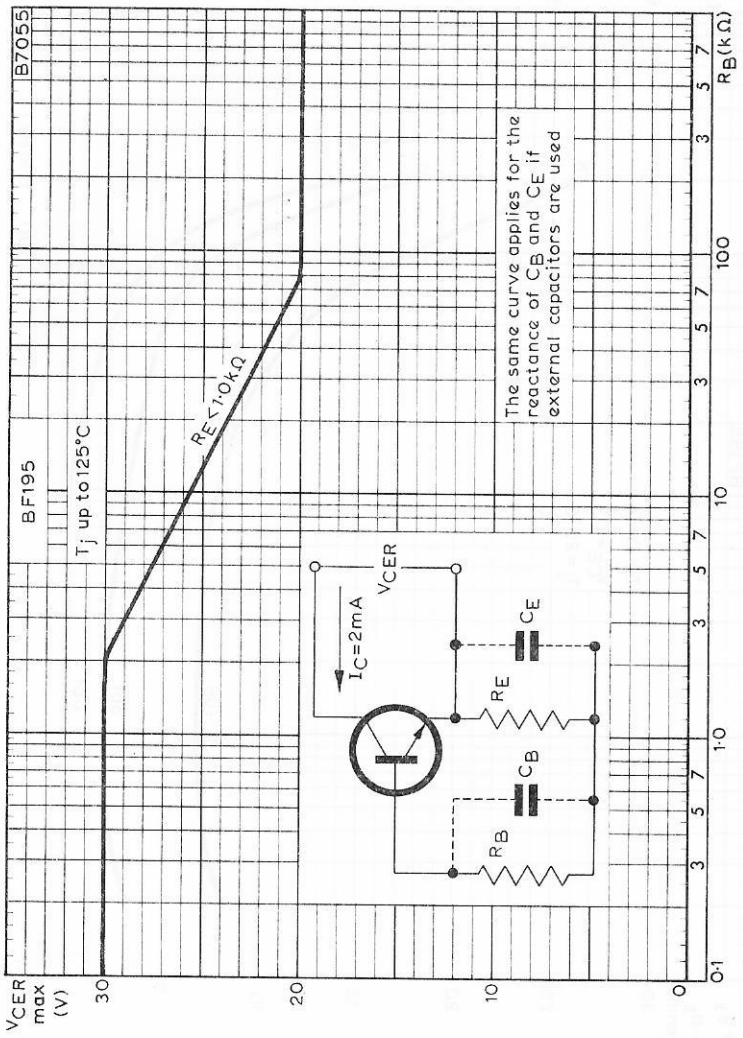
MUTUAL CHARACTERISTICS. $T_j = 25^oC$



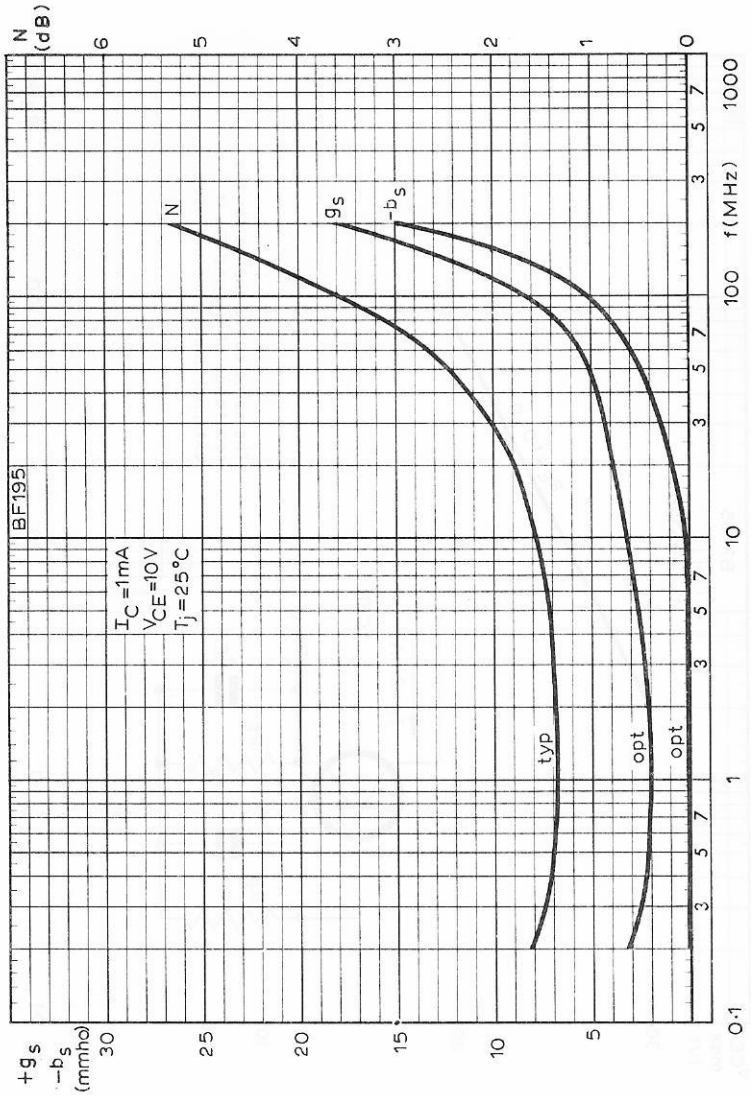
TYPICAL OUTPUT CHARACTERISTICS. $T_j = 25^oC$



TYPICAL STATIC FORWARD CURRENT TRANSFER RATIO PLOTTED AGAINST COLLECTOR CURRENT

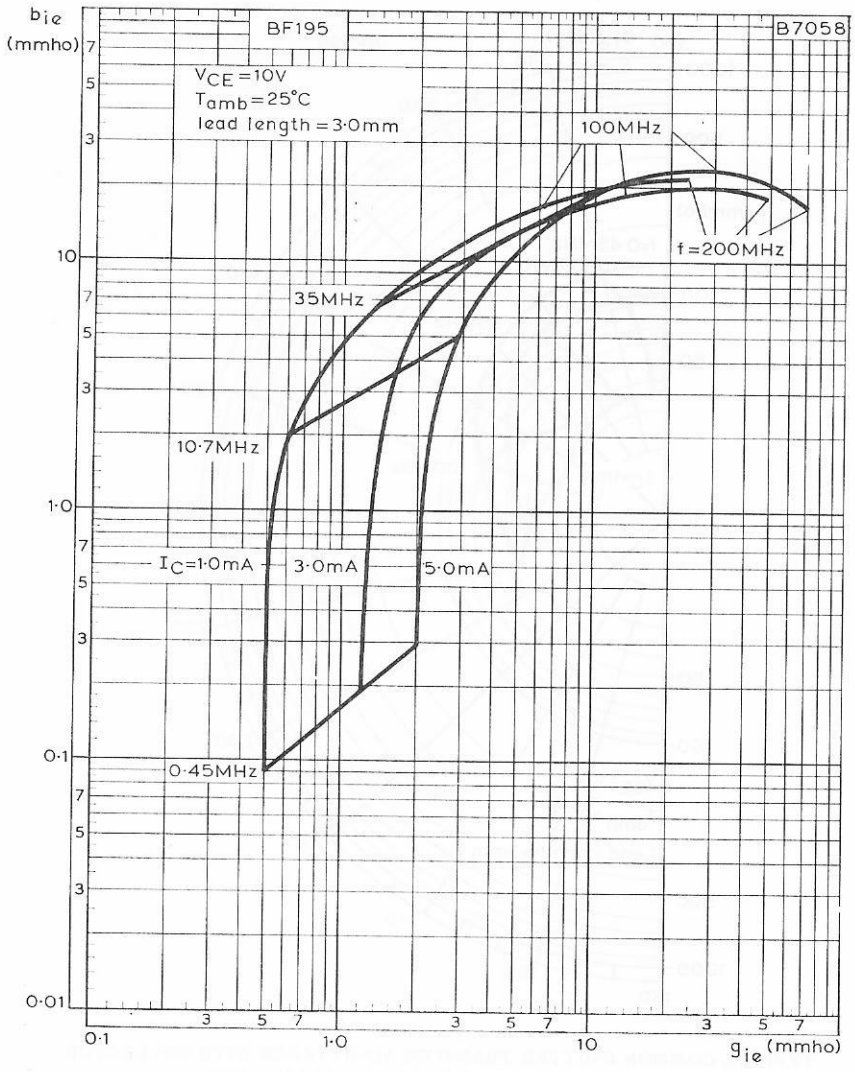


MAXIMUM COLLECTOR-EMITTER VOLTAGE PLOTTED AGAINST EXTERNAL BASE RESISTANCE

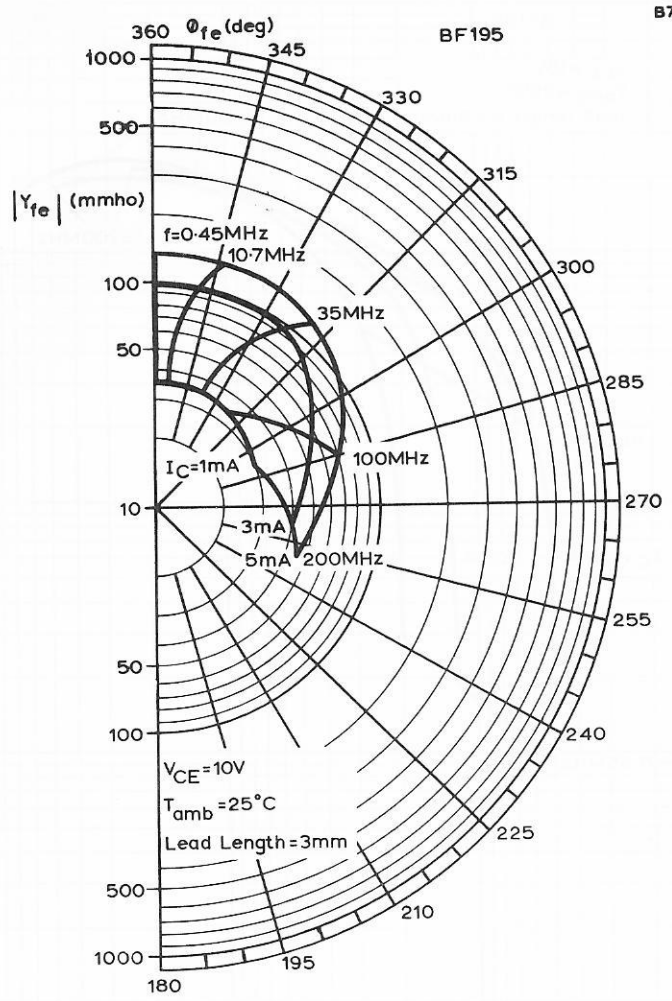


TYPICAL SOURCE CONDUCTANCE AND SOURCE SUSCEPTANCE PLOTTED AGAINST FREQUENCY AT OPTIMUM SOURCE ADMITTANCE

TYPICAL NOISE FIGURE PLOTTED AGAINST FREQUENCY AT OPTIMUM SOURCE CONDUCTANCE



TYPICAL COMMON EMITTER INPUT ADMITTANCE WITH COLLECTOR CURRENT AND FREQUENCY AS PARAMETERS



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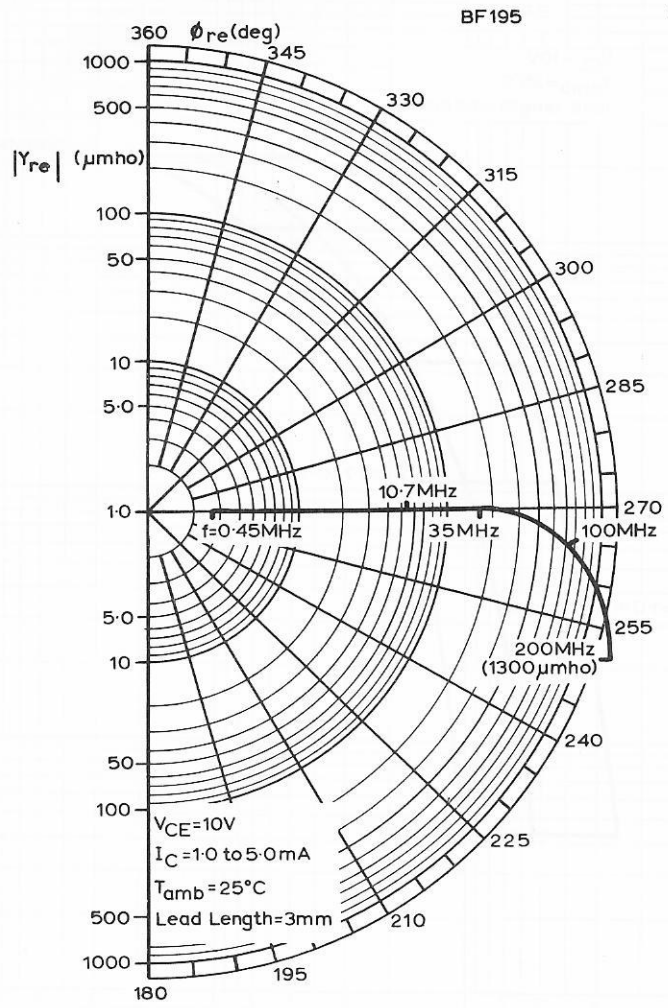
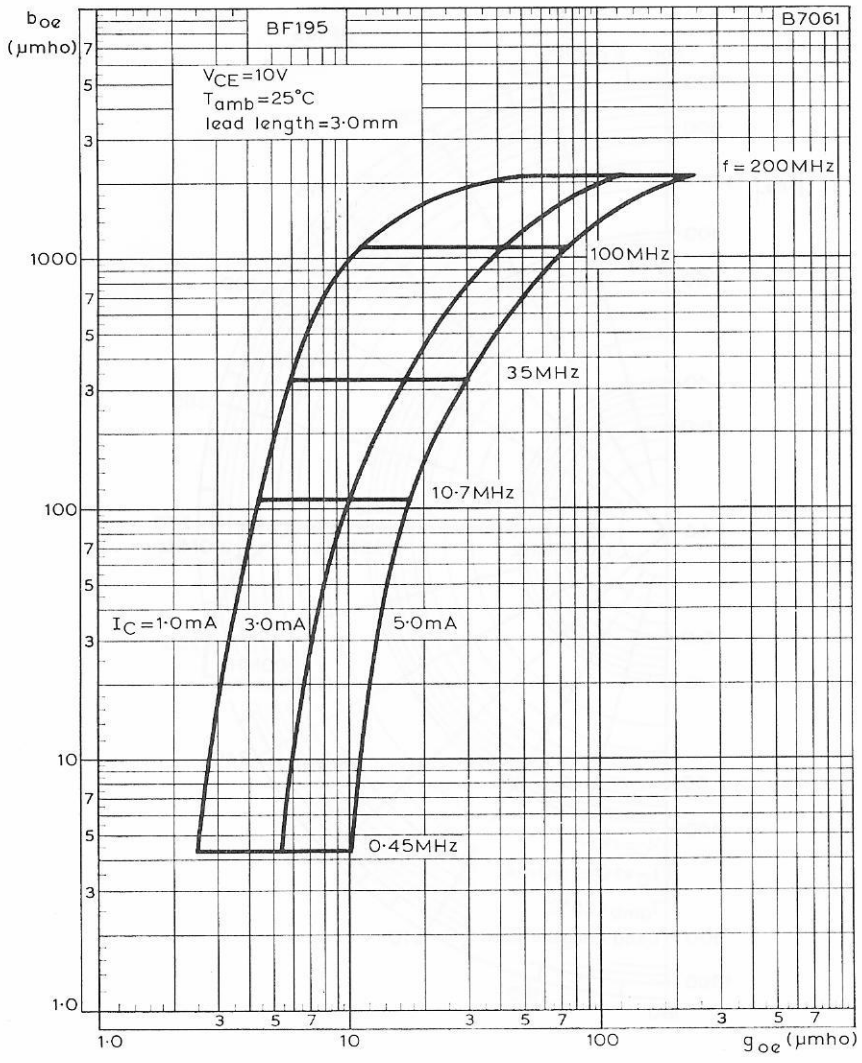


TYPICAL COMMON EMITTER FEEDBACK ADMITTANCE WITH COLLECTOR CURRENT AND FREQUENCY AS PARAMETERS



TYPICAL COMMON EMITTER OUTPUT ADMITTANCE WITH COLLECTOR CURRENT AND FREQUENCY AS PARAMETERS